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Minimization of Surface Impurities in Anodized Aluminum

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Minimization of Surface Impurities in Anodized Aluminum

Abstract

Anodized aluminum is commonly used to create wear-resistant parts for process tools used in the semiconductor industry. Sinc microchips require high purity manufacturing environments[1], surface impurities on tooling needs to be minimized.

It has been determined that anodized aluminum parts are one source of contamination. This project investigates the source of trace elements in anodized aluminum 6061 parts and ways to reduce them.

Disciplines

Materials Science and Engineering

College of Engineering

ISEDSTATE Minimization of Surface Impurities in Anodized Aluminum Logan Ward, Steven Livers, and Amber Huddleston

Anodized minimized.

to reduce them.

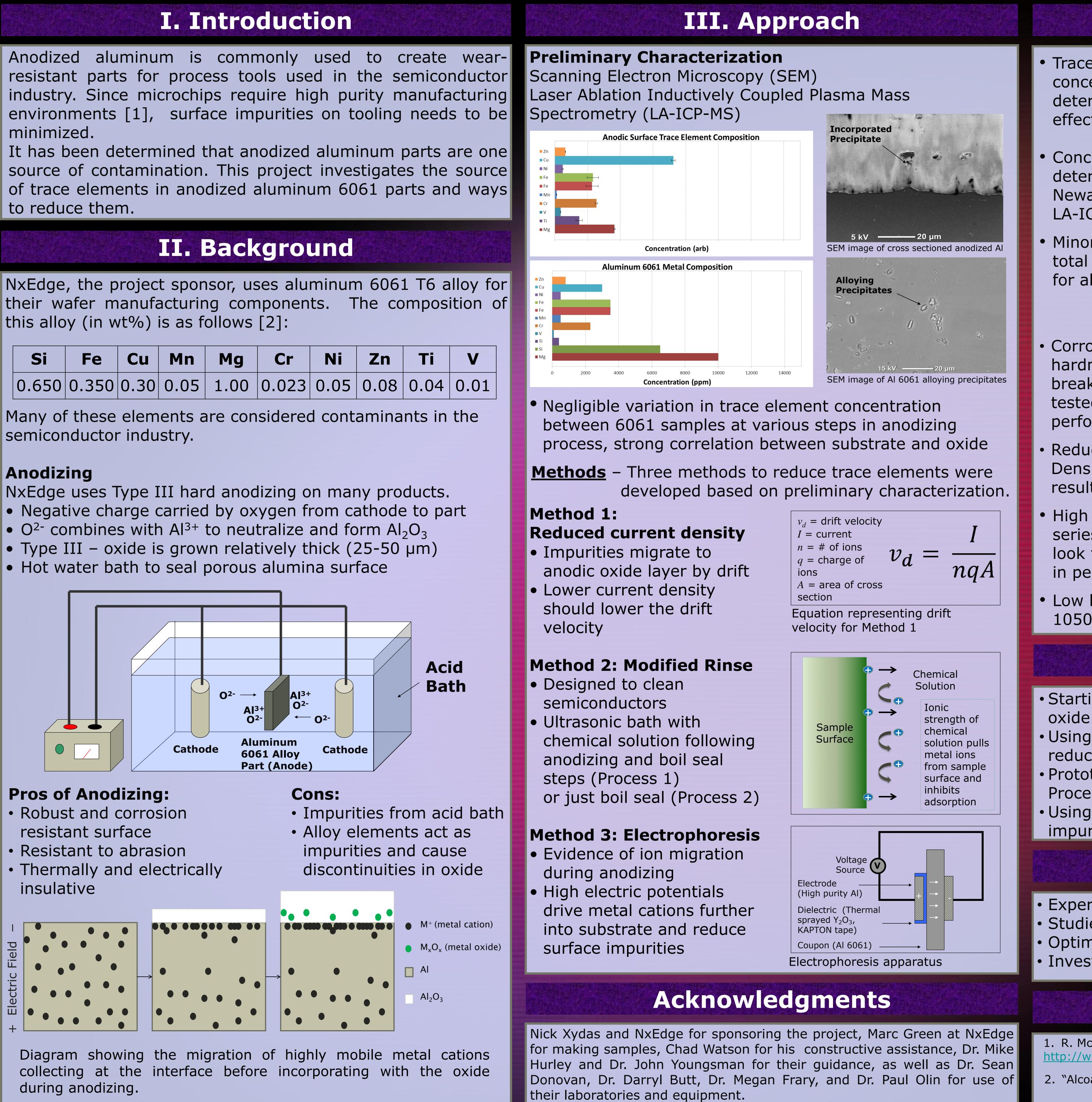
this alloy (in wt%) is as follows [2]:

Si	Fe	Cu	Mn	Mg	Cr	Ni	Zn	Т
0.650	0.350	0.30	0.05	1.00	0.023	0.05	0.08	0.0

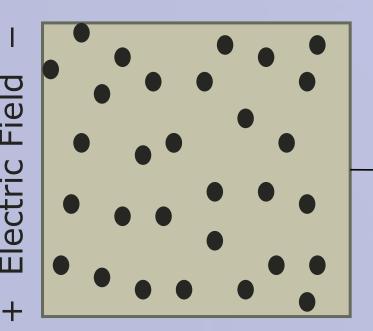
semiconductor industry.

Anodizing

- Hot water bath to seal porous alumina surface



- Robust and corrosion resistant surface
- Resistant to abrasion
- Thermally and electrically insulative



during anodizing.

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- Trace elements concentrations to determine method effectiveness
- Concentrations determined using a Newave Research LA-ICP-MS system.
- Minor decreases in total trace elements for all methods
- Corrosion resistance, hardness, and breakdown voltage tested to measure performance
- Reduced Current Density had best results
- High purity Al 1050 series was tested to look for any changes in performance
- Low breakdown for Al 1050 series

Reduced Current Density Modified Rinse Process 2

Breakdown Voltage Corrosion Resistance Hardnes: Normal Process (Control) **Reduced Current Density** Modified Rinse Process 1 Modified Rinse Process 2 Electrophoresis 4000 V Electrophoresis 500 V **Electrophoresis 19 A** High Purity 1050

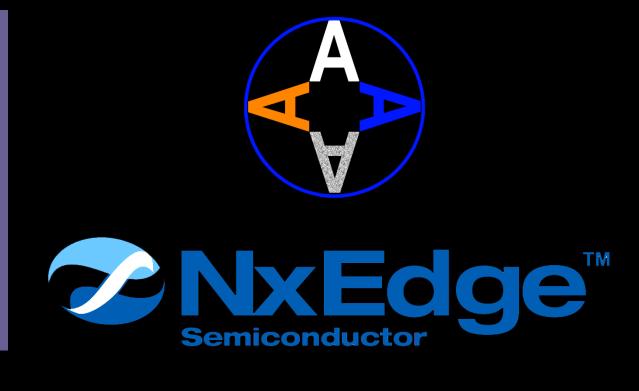
oxide layer

- reducing contaminants

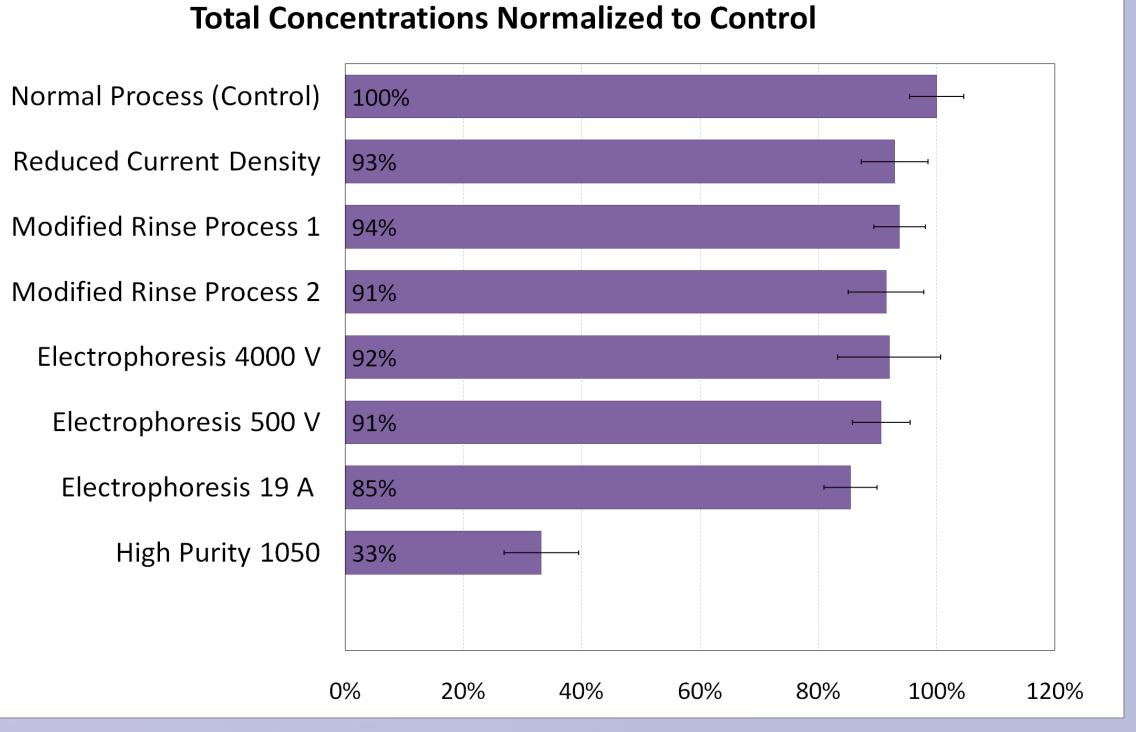
- Experimentation with various current densities or lower voltages

1. R. McFadden. A Basic Introduction to Clean Rooms. Available at: http://www.coastwidelabs.com/Technical%20Articles/Cleaning%20the%20Cleanroom.htm

2. "Alcoa Spectrochemical Standards," A. I. S. M. Division, Ed., ed. Pittsburgh, PA, 2004, p. 18.



V. Results



Performance Results Normalized to Control

VI. Conclusions

• Starting material is the main source of contaminant elements in the anodic • Using a high purity substrate or surface is the most effective method for • Prototypes created with Reduced Current Density or Modified Rinse Process 2 remained robust, crucial for reducing rate of contamination Using high purity aluminum substrate or coatings may drastically lower impurities while maintaining good hardness and corrosion resistance **VII. Future Work**

 Studies on bath life, dilution, and optimization of modified rinse process • Optimization of parameters for electrophoresis to achieve its full capabilities • Investigate use of coating with high purity aluminum prior to anodizing

References